

140 COMMERCE DRIVE MONTGOMERYVILLE, PA 18936-1013

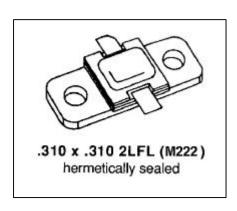
PHONE: (215) 631-9840 FAX: (215) 631-9855

## **MS2211**

# RF & MICROWAVE TRANSISTORS AVIONICS APPLICATIONS

#### **Features**

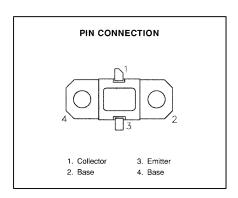
- 960-1215 MHz
- COMMON BASE
- GOLD METALLIZATION
- POUT = 6 W MIN. WITH 9.3 dB GAIN
- 5:1 VSWR CAPABILITY



#### **DESCRIPTION:**

The MS2211 is a silicon NPN bipolar device designed For specialized avionics applications, including JTIDS, utilizing pulse formats with short pulse widths and high burst rates or overall duty cycles.

The MS2211 is housed in a hermetic package and utilizes internal input impedance matching. Gold metallization and emitter ballasting assures high reliability under operating conditions.



## ABSOLUTE MAXIMUM RATINGS (Tcase = 25°C)

Symbol	Parameter	Value	Unit
P <sub>DISS</sub>	Power Dissipation* (T <sub>C</sub> ≤ 75°C)	25	W
Ic	Device Current*	0.9	Α
V <sub>cc</sub>	Collector-Supply Voltage	32	V
TJ	Junction Temperature (Pulsed RF Operation)	+250	°C
T <sub>STG</sub>	Storage Temperature	-65 to +200	°C

#### Thermal Data

R <sub>TH(J-C)</sub> Ju	unction-case Thermal Resistance*	7.0	°C/W
-------------------------	----------------------------------	-----	------

<sup>\*</sup> Applies only to rated RF amplifier operation



# **MS2211**

# ELECTRICAL SPECIFICATIONS (Tcase = 25°C)

# **STATIC**

Symbol	Test Conditions			Value		
			Min.	Тур.	Max.	Unit
BV <sub>CBO</sub>	I <sub>C</sub> = 1mA	I <sub>E</sub> = 0mA	48			٧
BV <sub>CER</sub>	I <sub>C</sub> = 5mA	$R_{BE} = 10 \Omega$	48			٧
BV <sub>EBO</sub>	I <sub>E</sub> = 1mA	I <sub>C</sub> = 0 mA	3.5			٧
I <sub>CES</sub>	V <sub>CE</sub> = 28 V	$V_{BE} = 0 V$			0.5	mA
h <sub>FE</sub>	V <sub>CE</sub> = 5 V	I <sub>C</sub> = 250mA	30		300	

#### **DYNAMIC**

Symbol	Test Conditions			Value			
Symbol			Min.	Тур.	Max.	Unit	
P <sub>out</sub>	f = 960-1215 MHz	V <sub>CC</sub> = 28V	$P_{IN} = 0.7W$	6.0			W
G <sub>P</sub>	f = 960-1215 MHz	V <sub>CC</sub> = 28V	P <sub>IN</sub> = 0.7W	9.3			dB
η	f = 960-1215 MHz	$V_{CC} = 28V$	$P_{IN} = 0.7W$	45			%

Pulse Format: 6.4  $\mu$ S ON/ 6.6  $\mu$ S OFF, repeat for 3mS, then OFF for 4.5125mS.

Conditions Duty Cycle: Burst: 49.2%, overall 20.8%

#### **IMPEDANCE DATA**

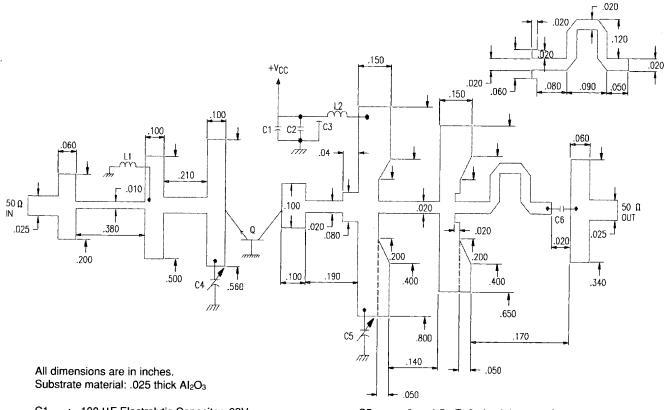
FREQ	$Z_IN(\Omega)$	$Z_{CL}(\Omega)$	
960 MHz	8.2 + j8.5	10.5 + j12.9	
1090 MHz	11.1 + j8.3	9.4 + j11.3	
1215 MHz	15.6 + j6.8	9.0 + j8.3	

 $P_{IN} = 0.7W$  $V_{CC} = 28V$ 



# **MS2211**

## **TEST CIRCUIT**



: 100 µF Electrolytic Capacitor, 63V : .1 µF Ceramic Capacitor C2

СЗ

: Feedthrough Bypass SCI 712-022

: .6 — 4.5 pF, 2 pls, Johanson Gigatrim Capacitor

C5 .6 — 4.5 pF, 2 pls, Johanson Gigatrim Capacitor

C6 100 pF Chip Capacitor

L1 No. 26 Wire, 4 Turn

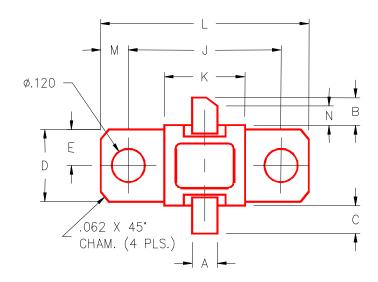
L2 : No. 26 Wire, 4 Turn

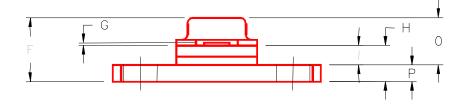




## PACKAGE MECHANICAL DATA

## PACKAGE STYLE M222





	MINIMUM	MAXIMUM		MINIMUM	MAXIMUM	
	INCHES/MM	INCHES/MM		INCHES/MM	INCHES/MM	
Α	.100/2,54		J	.562/14,28		
В	.110/2,80		K	.310/7,87		
С	.110/2,80		L	.800/	20,32	
D	.296/7,52		М	.119/3,02		
E	.148/3,76		N	.050/1,27		
F		.230/5,84	0		.170/4,32	
G	.003/0,08	.006/0,15	Р	.062/1,58		
Н	.118/3,00	.131/3,33				
	.059,	/1,50				